

L27: (884) 3 near 9 25  
L28: (4) 23 same 27  
L30: (24) 28 and 7  
L28: (86) 23 and 27  
L31: (253574) 3.cfm.  
L32: (2609) 23.cfm.  
L33: (881) 25.cfm.  
L34: (0) 32 with 33  
L35: (295030) 24.cfm.  
L36: (84) 35 with 32  
L37: (64) 3 with 36  
L38: (2608848) source  
L38: (10) 36 with 38  
L40: (3634203) "including"  
L41: (10) 36 with 40  
L42: (12) 36 same 40  
L43: (8160780) formed  
L44: (23) 43 with 38  
L45: (0) 33 with 36  
L46: (2) "08143836"  
L47: (143) (257/325).CCLS.  
L48: (703) (257/325,324).CCLS.  
L48: (2) 48 and 32  
L50: (9) 49 and 23

Failed  
Saved

Browse Queue Clear  
DBs: USPAT:US PGPUB:EPO:JPO:DERWENT:IBM:TDC  
Default operator: OR

Plurals

Highlight all hit terms initially

48 and 23

Sept 2004

	U	S	Inventor	Document	Year	P	Title	Current	Current	Current	Retrieval	S	C	P	Image	Doc	P
1			Ogura, Seiki	US 6886632	2004	2	Dual-bit multi-level ballistic MONOS memory	257/374	257/325			R	F	F	F	US 688663	
2			Kim, Seong-G	US 2004015	2004	1	Non-volatile SONOS memory device and met	257/324				F	F	F	F	US 200401	
3			Letavic, Tod	US 2003006	2003	1	SELF-ALIGNED DUAL-OXIDE UMOSFET DEVI	257/330	257/324			R	F	F	F	US 200300	
4			Vyvoda, Mich	US 6710409	2004	1	Inverted staggered thin film transistor with a	257/347	257/315			F	F	F	F	US 671040	
5			Nakao, Hiron	US 5589700	1996	1	Semiconductor nonvolatile memory	257/325	257/410			R	F	F	F	US 558970	
6			Hong, Gary	US 5414287	1995	1	Process for high density split-gate memory c	257/316	257/322			R	F	F	F	US 541428	
7			Shimoji, Nori	US 5318228	1994	1	Semiconductor nonvolatile memory with wid	257/324	257/406			F	F	F	F	US 531822	
8			Iwai, Hiroshi	US 5237188	1993	5	Semiconductor device with nitrided gate ins	257/325	257/411			R	F	F	F	US 523718	
9			Rosler, Bern	US 4087795	1978	4	Memory field effect storage device	385/185	257/321			F	F	F	F	US 408779	

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